

Electronic Supplementary Information

Optimization of metal-to-insulator phase transition properties in polycrystalline VO₂ films for terahertz modulation applications by doping

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Table S1 Electrical MIT Properties of VO₂ samples obtained at different Nb contents.

sample	Nb Content (%)	T _{TH} (°C)	T _{TC} (°C)	T _C (°C)	ΔH (°C)	FWHM (°C)	
						Heating	cooling
S1	0.0	70.8	53.6	62.2	17.2	6.1	8.6
S2	2.6	52.0	44.2	48.1	7.8	6.3	6.8
S3	4.3	44.8	37.9	41.35	6.9	6.8	6.9
S4	6.5	35.9	30.7	33.3	5.2	9.7	9.4

Table S2 Electrical MIT Properties of VO₂ samples obtained at different W contents.

sample	W content (%)	T _{TH} (°C)	T _{TC} (°C)	T _C (°C)	ΔH (°C)	FWHM (°C)	
						Heating	cooling
S5	0.0	72.3	56.1	64.2	16.2	6.2	7.5
S6	1.1	64.6	52.3	58.45	12.3	7.8	6.9
S7	1.5	49.2	42.3	45.75	6.9	8.3	10.1